

CT60AM-18C

Insulated Gate Bipolar Transistor

REJ03G0287-0100

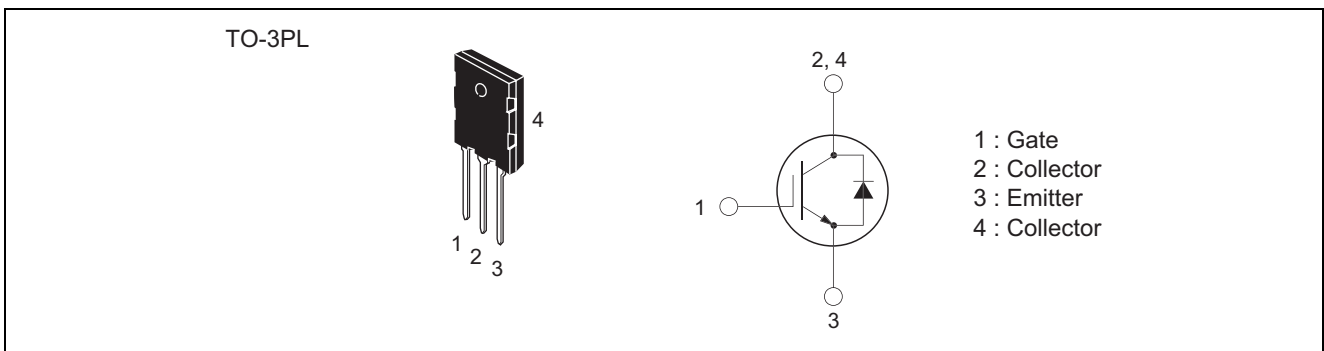
Rev.1.00

Aug.20.2004

Features

- V_{CES} : 900 V
- I_C : 60 A
- Integrated fast-recovery diode
- For voltage-resonance

Appearance Figure



Applications

Voltage-resonance type home appliances (Microwave ovens, IH cooking devices, IH rice-cookers)

Maximum Ratings

($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V_{CES}	900	V	$V_{GE} = 0\text{ V}$
Gate-emitter voltage	V_{GES}	± 20	V	$V_{CE} = 0\text{ V}$
Peak gate-emitter voltage	V_{GEM}	± 30	V	$V_{CE} = 0\text{ V}$
Collector current	I_C	60	A	
Collector current (Pulse)	I_{CM}	120	A	
Emitter current	I_E	40	A	
Maximum power dissipation	P_C	200	W	$T_c = 25^\circ\text{C}$
Junction temperature	T_j	- 40 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +150	$^\circ\text{C}$	

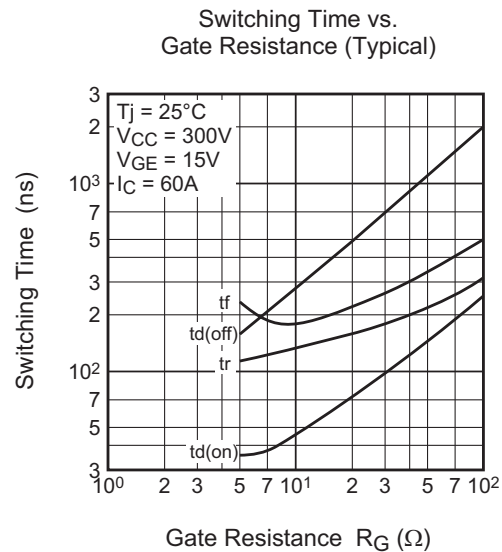
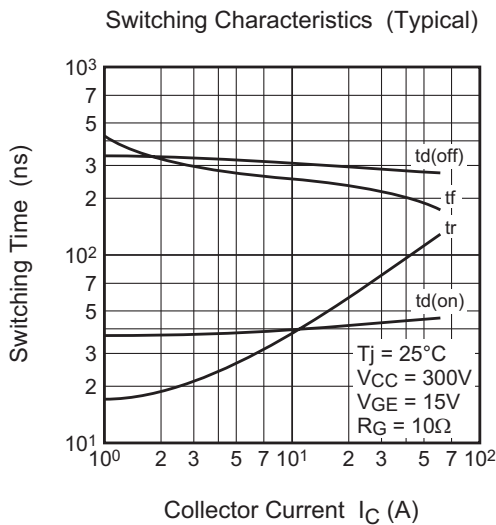
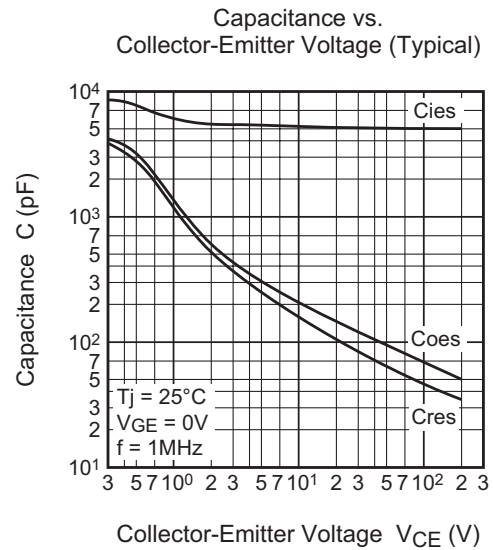
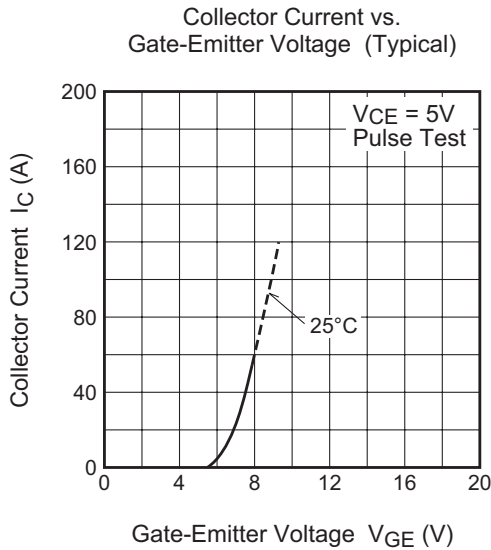
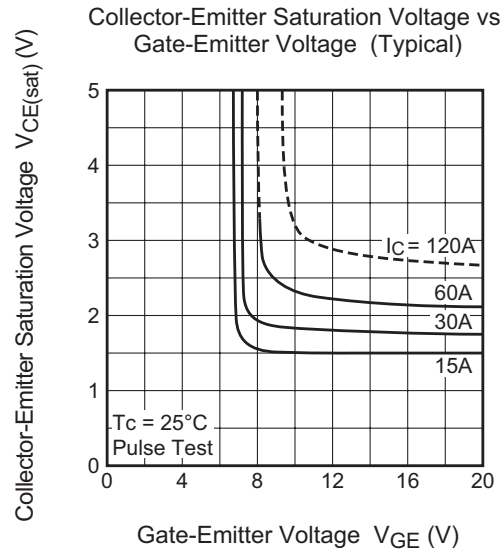
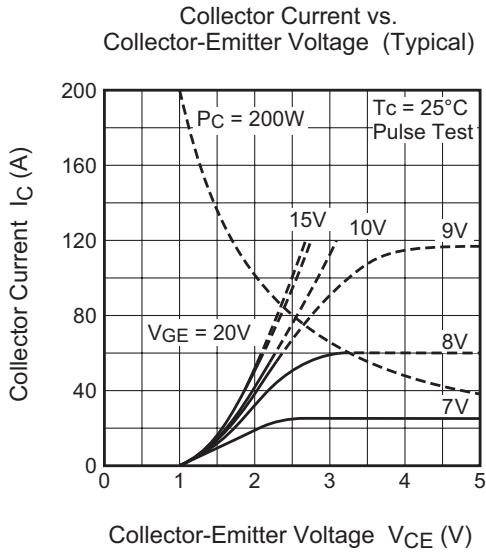
Electrical Characteristics

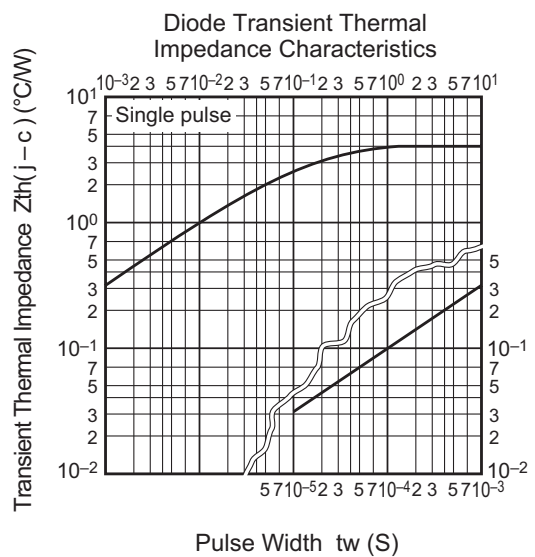
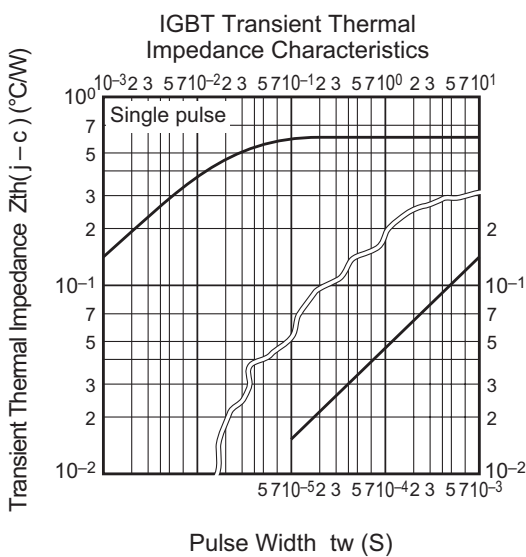
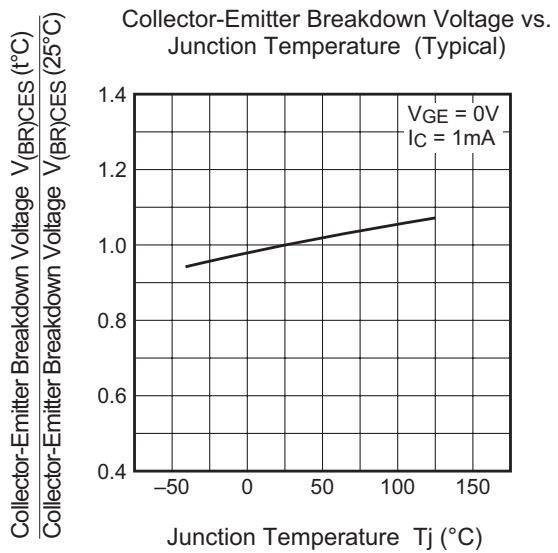
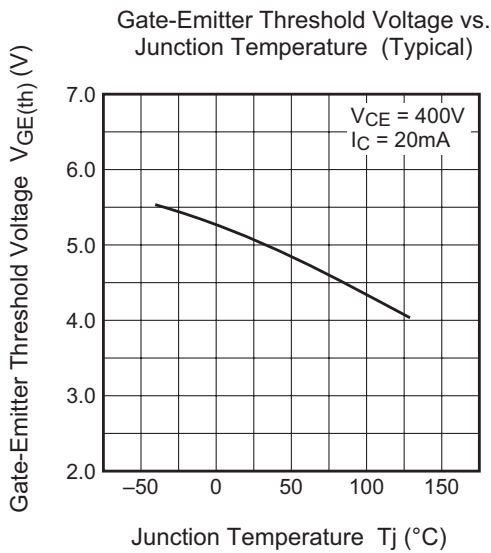
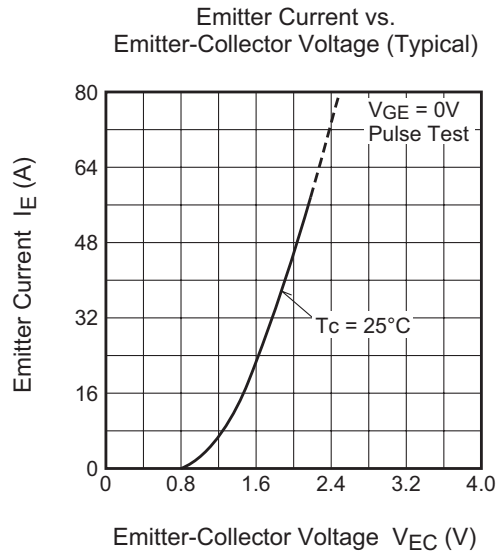
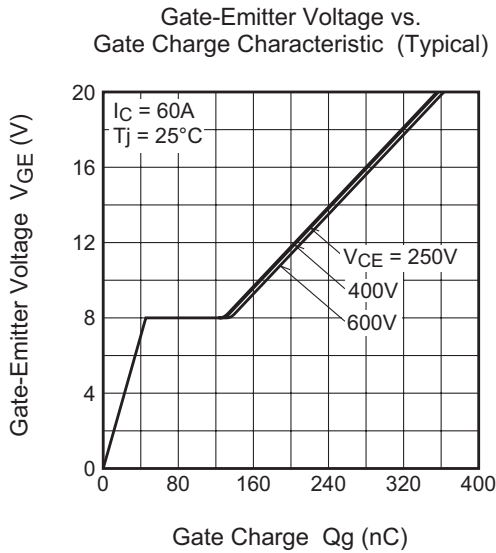
(Unless otherwise specified, T_j = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	V _{(BR)CES}	1000 ^{not e1}	—	—	V	I _C = 1 mA, V _{GE} = 0 V
Collector-emitter leakage current	I _{CES}	—	—	1	mA	V _{CE} = 900 V, V _{GE} = 0 V
Gate-emitter leakage current	I _{GES}	—	—	±0.5	μA	V _{GE} = ±20 V, V _{CE} = 0 V
Gate-emitter threshold voltage	V _{GE(th)}	2.0	4.0	6.0	V	I _C = 6 mA, V _{CE} = 10 V
Collector-emitter saturation voltage	V _{CE(sat)}	—	2.0	2.7	V	I _C = 60 A, V _{CE} = 15 V
Input capacitance	C _{iss}	—	5000	—	pF	V _{CE} = 25 V, V _{GE} = 0 V, f = 1MHz
Output capacitance	C _{oss}	—	125	—	pF	
Reverse transfer capacitance	C _{rss}	—	85	—	pF	
Turn-on delay time	t _{d(on)}	—	0.05	—	μs	I _C = 60 A, Resistive loads, V _{CC} = 300 V, V _{GE} = 15 V, R _G = 10 Ω
Rise time	t _r	—	0.12	—	μs	
Turn-off delay time	t _{d(off)}	—	0.30	—	μs	
Fall time	t _f	—	0.25	—	μs	
Tail loss	E _{tail}	—	0.6	1.0	mJ/pls	I _{CP} = 60 A, T _j = 125°C, dv/dt = 200 V/μs, Single-device voltage resonance circuit
Tail current	I _{tail}	—	6	12	A	
Emitter-collector voltage	V _{EC}	—	—	3	V	I _E = 60 A, V _{GE} = 0 V
Diode reverse recovery time	t _{rr}	—	0.5	2	μs	I _E = 60 A, di/dt = 20 A/μs
Thermal resistance (IGBT)	R _{th(j-c)}	—	—	0.625	°C/W	Junction to case
Thermal resistance (Diode)	R _{th(j-c)}	—	—	4.0	°C/W	Junction to case

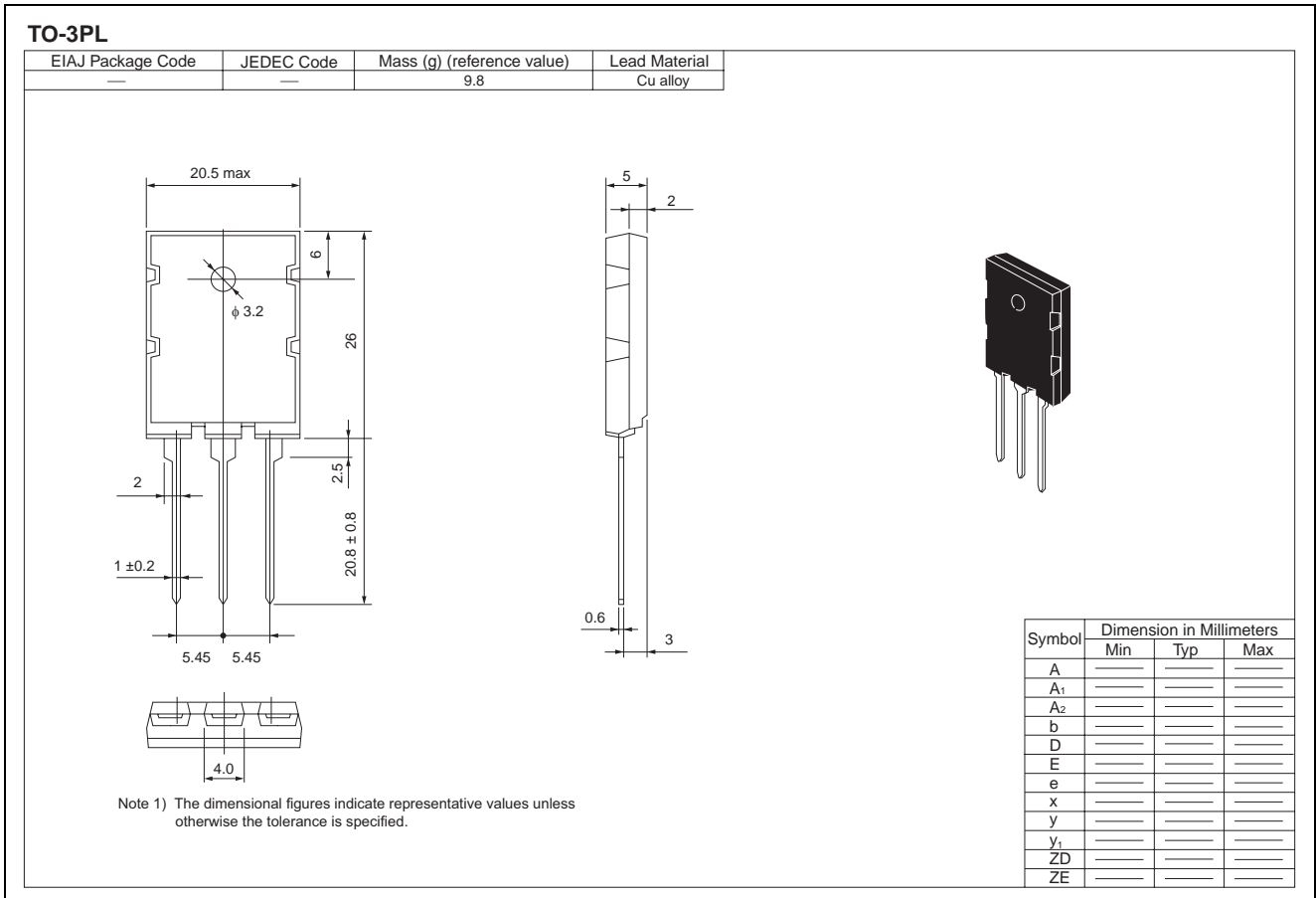
Notes: 1 Selected value

Performance Curves





Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	25	Type name	CT60AM-18C
Lead form	Plastic Magazine (Tube)	25	Type name – Lead forming code	CT60AM-18C-AD

Note : Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
 2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
 3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors.
Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (<http://www.renesas.com>).
 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
 5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
 6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
 7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
 8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.
-



RENESAS SALES OFFICES

<http://www.renesas.com>

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500 Fax: <1> (408) 382-7501

Renesas Technology Europe Limited.

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, United Kingdom
Tel: <44> (1628) 585 100, Fax: <44> (1628) 585 900

Renesas Technology Europe GmbH

Dornacher Str. 3, D-85622 Feldkirchen, Germany
Tel: <49> (89) 380 70 0, Fax: <49> (89) 929 30 11

Renesas Technology Hong Kong Ltd.

7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2375-6836

Renesas Technology Taiwan Co., Ltd.

FL 10, #99, Fu-Hsing N. Rd., Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

26/F., Ruijin Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001